

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1751	((In with Ga with N) or (indium near2 gallium near2 nitride)) and (nitride near2 semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/28 16:28
L6	26	clad\$3 and active and substrate and (In"y"Ga"1-y" N or In"y"Ga"1-x" N or In"z"Ga"1-z" N or (In near2 "y" near2 Ga near2 "1-y" near2 N) or (In near2 "x" near2 Ga near2 "1-x" near2 N) or (In near2 "z" near2 Ga near2 "1-z" near2 N))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:29
L4	75	(nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:29
L3	125	(nitride near2 semiconductor) and clad\$3 and active and substrate and (conductivity or guide or buffer) and (In with Ga with N)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:29
L2	135	clad\$3 and active and substrate and ((In"y"Ga"1-y" N or In"y"Ga"1-x" N or In"z"Ga"1-z" N or (In near2 "y" near2 Ga near2 "1-y" near2 N) or (In near2 "x" near2 Ga near2 "1-x" near2 N) or (In near2 "z" near2 Ga near2 "1-z" near2 N)) or (indium near2 gallium near2 (nitride or nitrogen)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/04/28 16:29
L9	1	(clad\$5 near (region or layer or medium)) and (active near (region or layer or medium)) and substrate and laser and ((conductiv\$5 or core) near2 (type or region or layer or medium)) and (In"y"Ga"1-x" N) AND ELECTRODE	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/28 16:30
L8	277	(clad\$5 near (region or layer or medium)) and (active near (region or layer or medium)) and substrate and laser and ((conductiv\$5 near type) and (nitride, near2 semiconductor))	US-PGPUB	OR	ON	2006/04/28 16:30
L7	3	((conduct\$7 near1 (layer or region or medium)) with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/28 16:30
L5	295	(clad\$5 near (region or layer or medium)) and (active near (region or layer or medium)) and substrate and laser and ((conductiv\$5 near type) and (nitride near2 semiconductor))	USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/28 16:30
L16	84	5 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
L15	115	1 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
L14	80	10 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
L13	0	9 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
L12	44	8 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31

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L11	1	6 and "372"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31
L10	200	(clad\$5) and (active) and substrate and laser and (conductiv\$5 or core) and (In NEAR4 Ga NEAR4 N) AND ELECTRODE	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 16:31